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Power Matters[™]

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Overview **Diagrams**

Electrical Rating	Symbol	Min	Тур	Max	Unit
Collector to Emitter Saturation Voltage	V _{CE(sat)}			0.50	V
DC Current Gain	HFE	50.00		300.00	

Maximum Electrical Rating	Symbol	Min	Тур	Max	Unit
Breakdown Voltage, Collector-Base (Emitter Open)	V _{BR(CBO)}			600.00	V
Collector Current (dc)	I _C			1.00	А
Collector-Emitter Voltage (Base Open)	V _{CEO}			600.00	V
Emitter-Base Voltage (Collector Open)	V _{EBO}			6.00	V
Power Dissipation, Total	P _T			4.00	W

This part can be found in the following product categories:

- → Discretes → Transistors → BJT(BiPolar Junction Transistor) → PNP Transistor
- $\bullet \ \ \, \text{Non-Radiation Hardened Devices} \ \bullet \ \, \text{Transistors} \ \bullet \ \, \text{BJT(BiPolar Junction Transistor)} \ \bullet \ \, \text{NPN Transistor}$

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